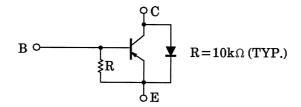
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

RN6006

Motor Drive Circuit Applications
Power Amplifier Applications
Power Switching Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Small flat package
- Pc = 1~2W (mounted on ceramic substrate)
- Complementary to RN5006

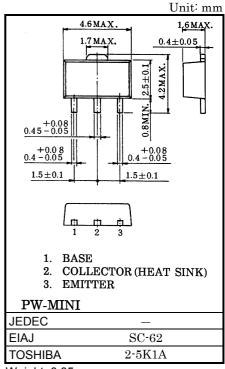
Equivalent Circuit



Maximum Ratings (Ta = 25°C)

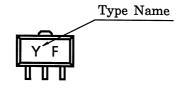
Characteristic		Symbol	Rating	Unit				
Collector-base voltage		V_{CBO}	-10	V				
Collector-emitter voltage		V _{CEO}	-10	V				
Emitter-base voltage		V _{EBO}	-6	٧				
Collector current	DC	IC	-2	Α				
	Pulse (Note1)	I _{CP}	-4					
Base current		ΙΒ	-0.4	Α				
Collector power dissipation		P_{C}	500	mW				
Collector power dissipation		P _C *	1000	mW				
Junction temperature		Tj	150	°C				
Storage temperature range		T _{stg}	-55~150	°C				
N . : D 1 : : ! ! . : 1 . :								

Note: Pulse width ≤ 10 ms, duty cycle ≤ 30 %



Weight: 0.05g

Marking



^{* :} Mounterd on ceramic substrate (250mm $^2 \times 0.8t$)

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Collector cut-offcurrent	I _{CBO}	_	$V_{CB} = -10V, I_E = 0$	_	_	-0.1	μΑ	
Emitter cut-off current	I _{EBO}	_	$V_{EB} = -6V, I_C = 0$	-0.462	-0.60	-0.857	mA	
Collector-emitter breakdown voltage	V _{(BR)CES}	_	I _C = −1mA	-10	_	_	٧	
DC current gain	h _{FE (1)}	_	$V_{CE} = -1V$, $I_{C} = -0.5A$	160	_	600	_	
	h _{FE (2)}		V _{CE} = -1V, IC = -4.0A	60	_	_		
Collector-emitter saturation voltage	V _{CE} (sat)	_	I _C = -2A, I _B = -0.05A	_	_	-0.5	V	
Transition frequency	f _T	_	V _{CE} = -1V, I _C = -0.5A	_	140	_	MHz	
Collector output capacitance	C _{ob}	_	V _{CB} = −10V, I _E = 0, f = 1 MHz	_	55	_	pF	
Resistor	R	_	_	7	10	13	kΩ	

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